

TSM060N03ECP

30V N-Channel Power MOSFET



Pin Definition:
 1. Gate
 2. Drain
 3. Source

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	6
	$V_{GS} = 4.5V$	9
Q_g	11.1	nC

Features

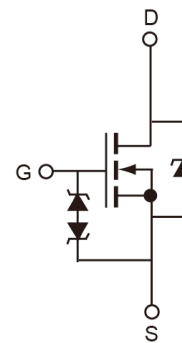
- Fast switching
- G-S ESD Protection Diode Embedded

Ordering Information

Ordering code	Package	Packing
TSM060N03ECP ROG	TO-252	2.5kpcs / 13" Reel

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET with ESD protection

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	70
		$T_C=100^\circ C$	44
Pulsed Drain Current ^(Note 1)	I_{DM}	280	A
Single Pulse Avalanche Energy ^(Note 2)	E_{AS}	88	mJ
Single Pulse Avalanche Current ^(Note 2)	I_{AS}	42	A
Total Power Dissipation	P_D	@ $T_C=25^\circ C$	54
		Derate above $T_C=25^\circ C$	0.43
Operating Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ C$

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	2.3	$^\circ C/W$
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	62	$^\circ C/W$

Electrical Specifications ($T_C=25^\circ\text{C}$ unless otherwise noted)

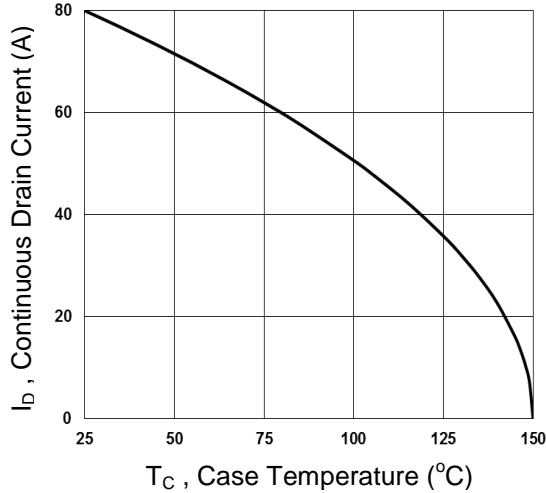
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	30	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 20A$	$R_{DS(ON)}$	--	4.8	6	m Ω
	$V_{GS} = 4.5V, I_D = 10A$		--	6.5	9	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	1	1.6	2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
	$V_{DS} = 24V, T_J = 125^\circ\text{C}$		--	--	10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	± 10	μA
Forward Transconductance	$V_{DS} = 10V, I_D = 10A$	g_{fs}	--	12.5	--	S
Dynamic						
Total Gate Charge ^(Note 3,4)	$V_{DS} = 15V, I_D = 20A,$ $V_{GS} = 4.5V$	Q_g	--	11.1	--	nC
Gate-Source Charge ^(Note 3,4)		Q_{gs}	--	1.85	--	
Gate-Drain Charge ^(Note 3,4)		Q_{gd}	--	6.8	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1\text{MHz}$	C_{iss}	--	1210	--	pF
Output Capacitance		C_{oss}	--	190	--	
Reverse Transfer Capacitance		C_{rss}	--	100	--	
Gate Resistance	$f = 1\text{MHz}$	R_g	--	2.5	--	Ω
Switching						
Turn-On Delay Time ^(Note 3,4)	$V_{DD}=15V, V_{GS}=10V,$ $R_G=3.3\Omega, I_D=-15A$	$t_{d(on)}$	--	7.5	--	ns
Turn-On Rise Time ^(Note 3,4)		t_r	--	14.5	--	
Turn-Off Delay Time ^(Note 3,4)		$t_{d(off)}$	--	35.2	--	
Turn-Off Fall Time ^(Note 3,4)		t_f	--	9.6	--	
Source-Drain Diode Ratings and Characteristic						
Continuous Drain-Source Diode		I_S	--	--	70	A
Pulse Drain-Source Diode		I_{SM}	--	--	280	A
Diode-Source Forward Voltage	$V_{GS} = 0V, I_S = 1A$	V_{SD}	--	--	1	V

Note:

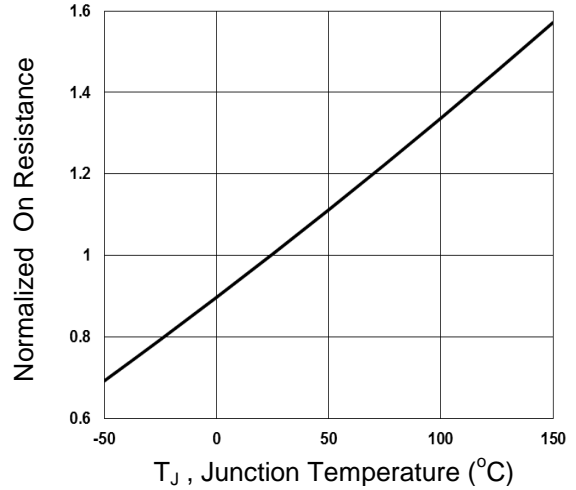
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=42A., R_G=25\Omega,$ Starting $T_J=25^\circ\text{C}$
3. The data tested by pulsed , pulse width $\leq 300\mu s,$ duty cycle $\leq 2\%$
4. Essentially independent of operating temperature.

Electrical Characteristics Curve

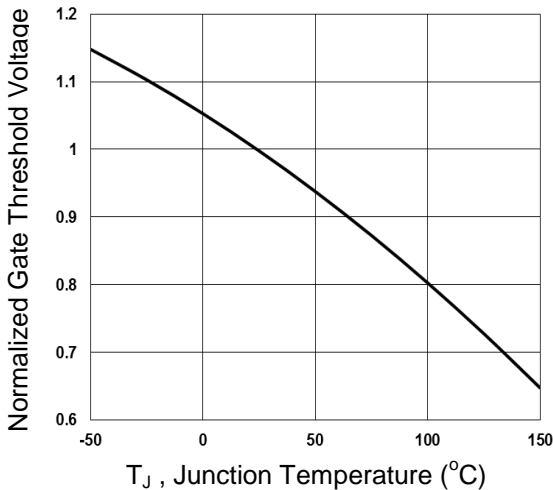
Continuous Drain Current vs. T_C



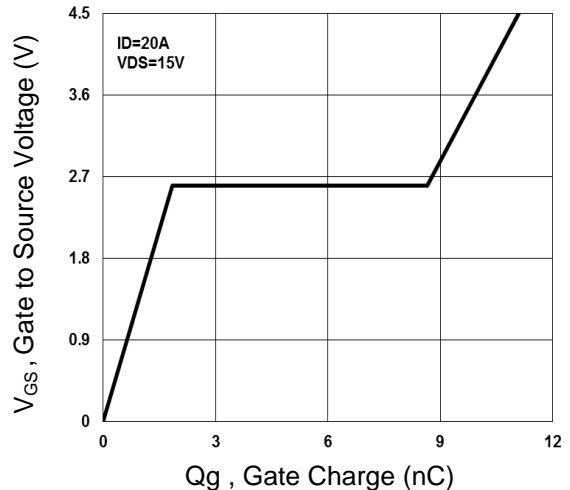
Normalized R_{DS(on)} vs. T_J



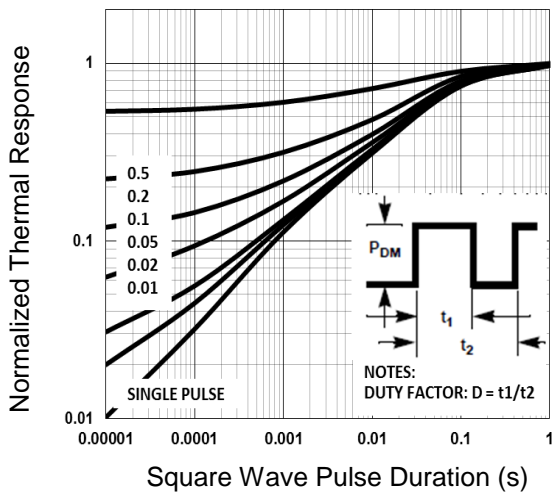
Normalized V_{th} vs. T_J



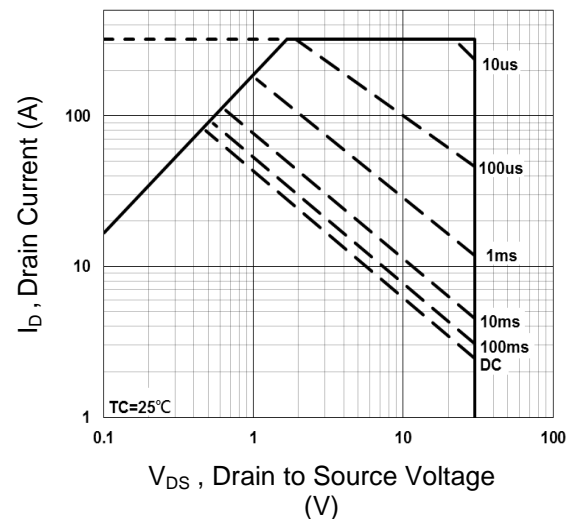
Gate Charge Waveform



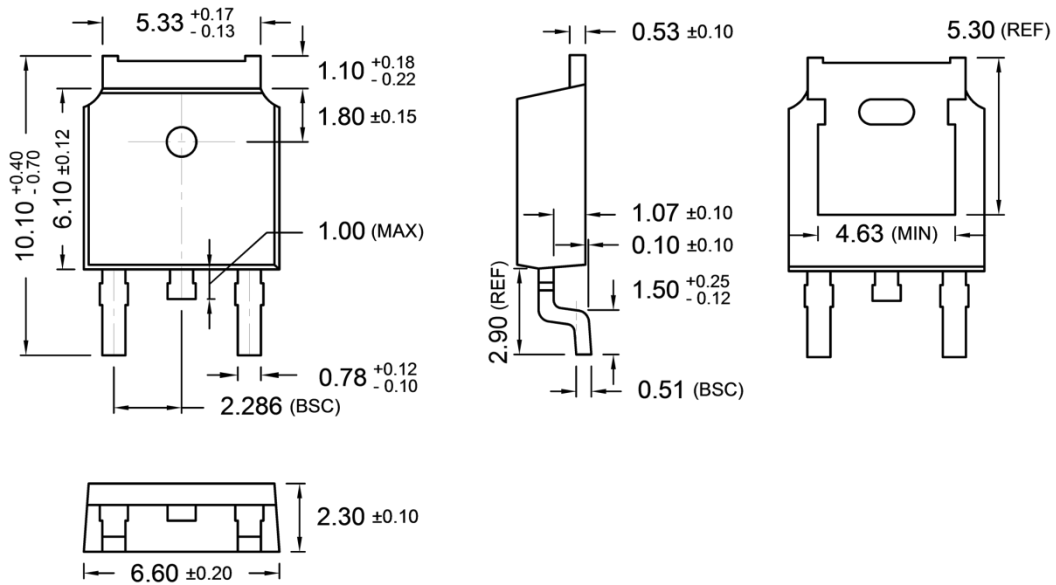
Normalized Transient Impedance



Maximum Safe Operation Area

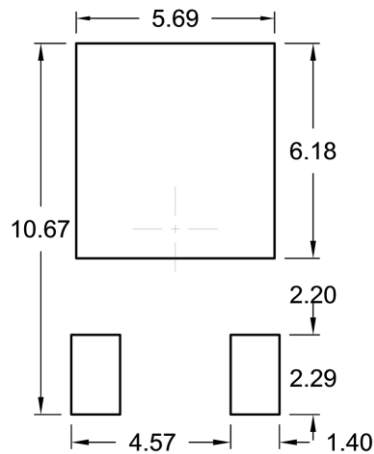


TO-252 Mechanical Drawing

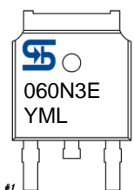


Unit: Millimeters

SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram



- Y = Year Code
- M = Month Code
- | | | | |
|--------|--------|--------|--------|
| O =Jan | P =Feb | Q =Mar | R =Apr |
| S =May | T =Jun | U =Jul | V =Aug |
| W =Sep | X =Oct | Y =Nov | Z =Dec |
- L = Lot Code (1~9, A~Z)

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Taiwan Semiconductor](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [JANTX2N5237](#) [FCA20N60_F109](#) [FDZ595PZ](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [TPCC8103,L1Q\(CM](#)
[MIC4420CM-TR](#) [VN1206L](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [SSM6J414TU,LF\(T](#) [751625C](#) [BUK954R8-60E](#)
[DMN3404LQ-7](#) [NTE6400](#) [SQJ402EP-T1-GE3](#) [2SK2614\(TE16L1,Q\)](#) [2N7002KW-FAI](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [ECH8691-](#)
[TL-W](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE221](#) [NTE2384](#) [NTE2903](#) [NTE2941](#) [NTE2945](#) [NTE2946](#) [NTE2960](#)
[NTE2967](#) [NTE2969](#) [NTE2976](#) [NTE455](#) [NTE6400A](#) [NTE2910](#) [NTE2916](#) [NTE2956](#) [NTE2911](#) [DMN2080UCB4-7](#) [TK10A80W,S4X\(S](#)
[SSM6P69NU,LF](#) [DMP22D4UFO-7B](#)